



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q64059

Shigeo ISHIKAWA

Appln. No.: 09/832,093

Group Art Unit: 2823

Confirmation No.: 8684

Examiner: Scott A. Brairton

Filed: April 11, 2001

For: FILM FORMING METHOD IN WHICH FLOW RATE IS SWITCHED

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated May 23, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please enter the following amended claims:

1. (Amended) A method of forming a film, comprising the steps of:
- (a) starting a supply of a reaction gas at a first flow rate into a chamber in which a plasma is formed, such that an initial film is formed on a wafer; and
- (b) starting a supply of the reaction gas at a second flow rate into the chamber in which the plasma is formed, after said step (a), while the supply of the reaction gas at said first flow rate continues such that the film is formed on the initial film, the first flow rate being smaller than the second flow rate.

6/a
8-26-02
Payton

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